

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	$I_D$ max $T_A = +25^\circ C$
30V	16m $\Omega$ @ $V_{GS} = 10V$	9.8A
	23m $\Omega$ @ $V_{GS} = 4.5V$	8.7A

## Description

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

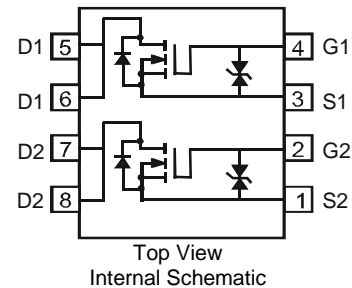
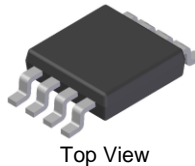
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

## Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.072 grams (Approximate)

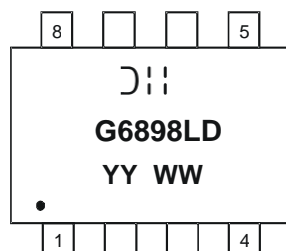


## Ordering Information (Notes 4 & 5)

Part Number	Qualification	Case	Packaging
DMG6898LSD-13	Commercial	SO-8	2,500 / Tape & Reel
DMG6898LSDQ-13	Automotive	SO-8	2,500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



= Manufacturer's Marking  
 G6898LD = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or YY = Year (ex: 14 = 2014)  
 WW = Week (01 - 53)

**Maximum Ratings** @ $T_A = +25^\circ\text{C}$  unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	20	V
Gate-Source Voltage			$V_{GSS}$	$\pm 12$	V
Continuous Drain Current (Note 6)	Steady State	$T_A = +25^\circ\text{C}$	$I_D$	9.5	A
		$T_A = +85^\circ\text{C}$		7.1	
Pulsed Drain Current (Note 7)			$I_{DM}$	30	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	$P_D$	1.28	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 6)	$R_{\theta JA}$	99.3	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** @ $T_A = +25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 8)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	20	-	-	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	$I_{DSS}$	-	-	1.0	$\mu\text{A}$	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	-	-	$\pm 10$	$\mu\text{A}$	$V_{GS} = \pm 12V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 8)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	1.0	1.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	11	16	m $\Omega$	$V_{GS} = 4.5V, I_D = 9.4A$
			17	23		$V_{GS} = 2.5V, I_D = 8.3A$
Forward Transfer Admittance	$ Y_{fs} $	-	17	-	S	$V_{DS} = 5V, I_D = 9.4A$
Diode Forward Voltage	$V_{SD}$	-	0.7	1.2	V	$V_{GS} = 0V, I_S = 1.3A$
<b>DYNAMIC CHARACTERISTICS (Note 9)</b>						
Input Capacitance	$C_{iss}$	-	1149	-	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	-	157	-	pF	
Reverse Transfer Capacitance	$C_{rss}$	-	142	-	pF	
Gate Resistance	$R_g$	-	1.51	-	$\Omega$	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$
Total Gate Charge ( $V_{GS} = 4.5V$ )	$Q_g$	-	11.6	-	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 9.4A$
Total Gate Charge ( $V_{GS} = 10V$ )	$Q_g$	-	26	-	nC	
Gate-Source Charge	$Q_{gs}$	-	2.7	-	nC	
Gate-Drain Charge	$Q_{gd}$	-	3.4	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	11.67	-	ns	$V_{DD} = 10V, V_{GS} = 4.5V, R_{GEN} = 6\Omega, I_D = 1A$
Turn-On Rise Time	$t_r$	-	12.49	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	35.89	-	ns	
Turn-Off Fall Time	$t_f$	-	12.33	-	ns	

- Notes:
6. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  7. Repetitive rating, pulse width limited by junction temperature.
  8. Short duration pulse test used to minimize self-heating effect.
  9. Guaranteed by design. Not subject to production testing.

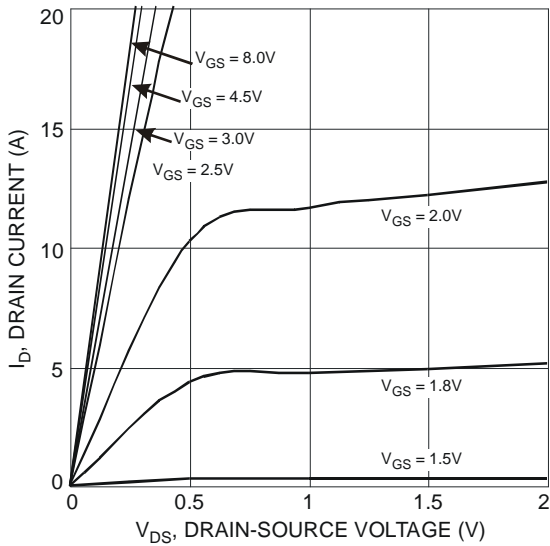


Fig. 1 Typical Output Characteristic

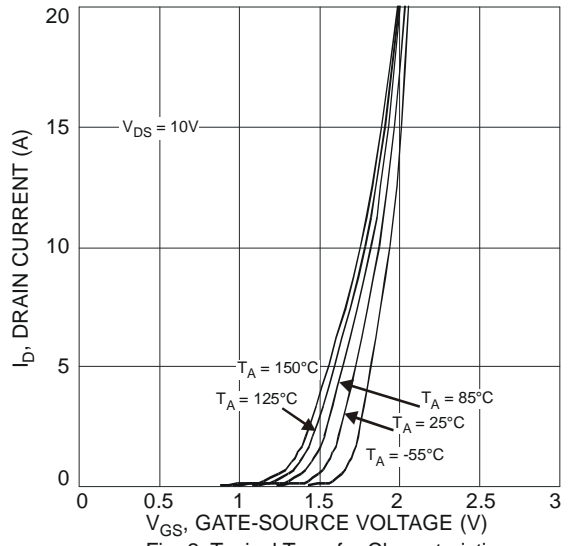


Fig. 2 Typical Transfer Characteristic

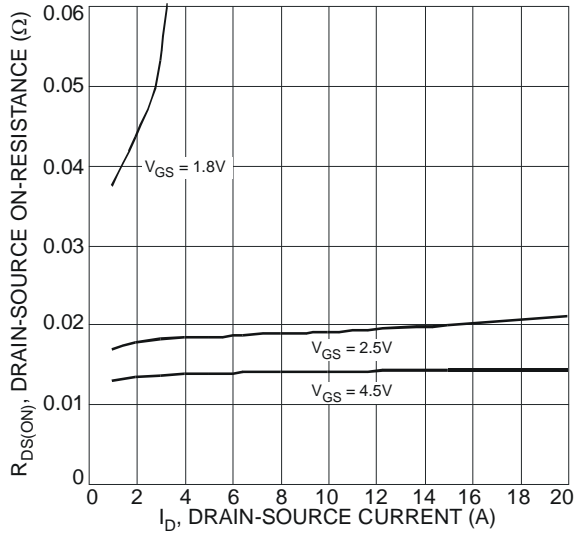


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

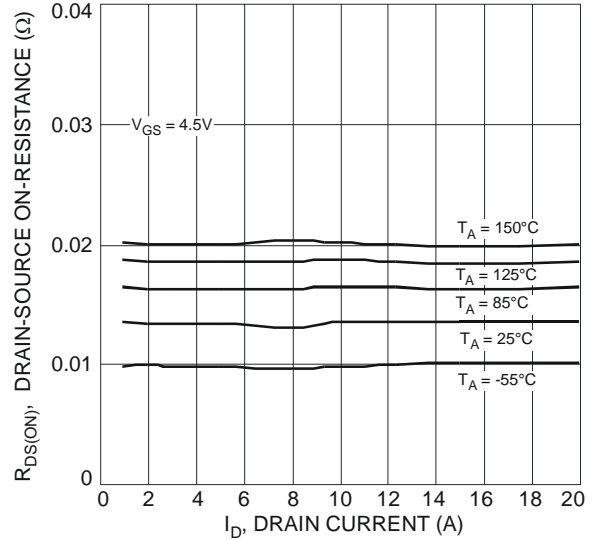


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

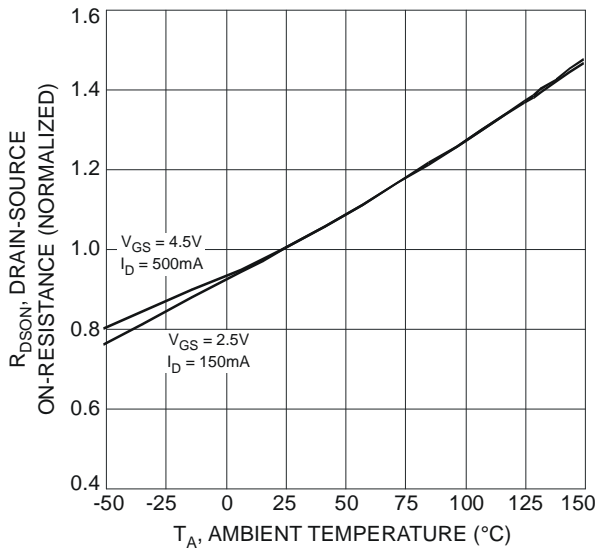


Fig. 5 On-Resistance Variation with Temperature

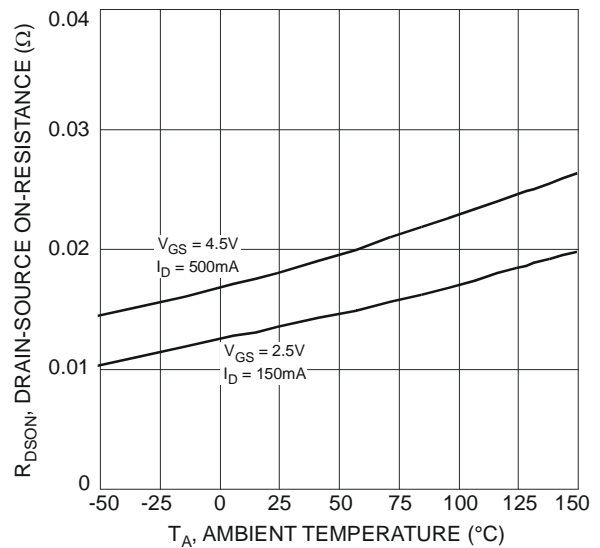


Fig. 6 On-Resistance Variation with Temperature

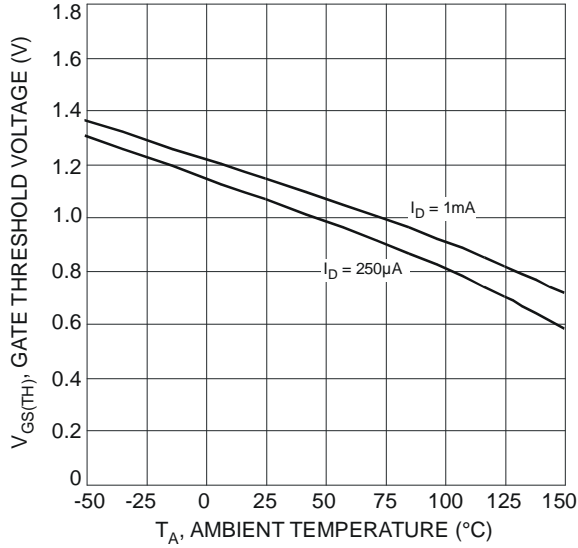


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

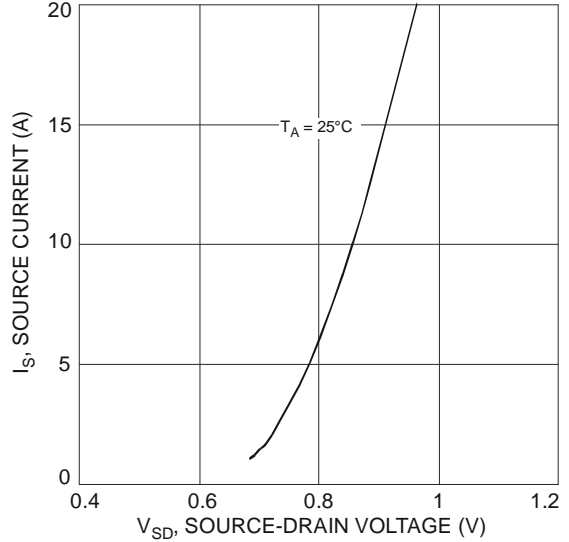


Fig. 8 Diode Forward Voltage vs. Current

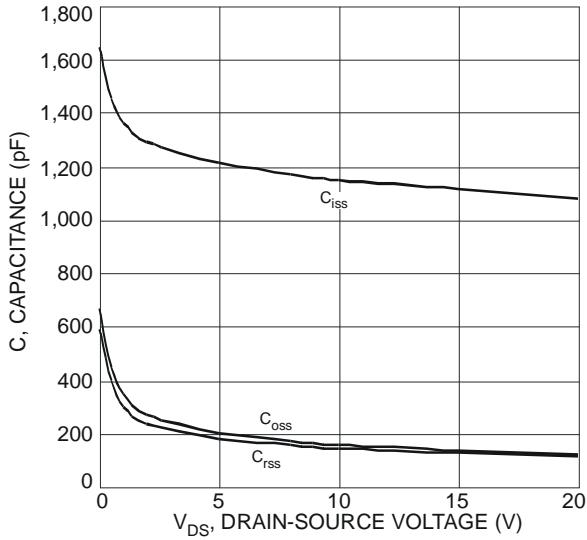


Fig. 9 Typical Total Capacitance

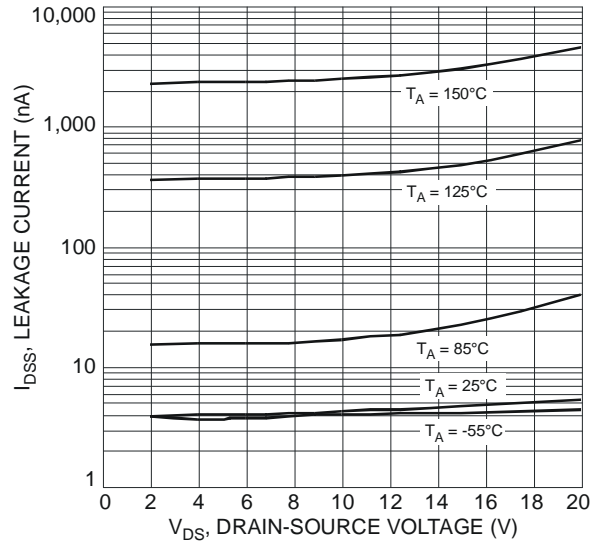


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

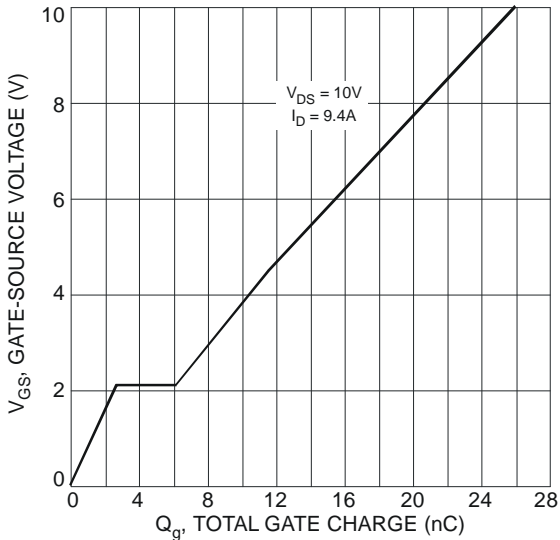


Fig. 11 Gate-Source Voltage vs. Total Gate Charge

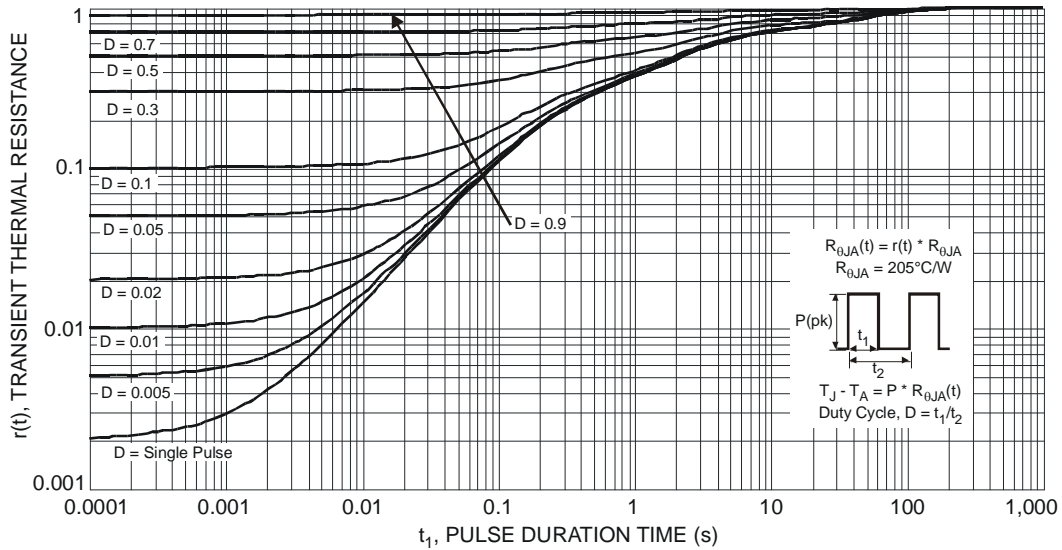
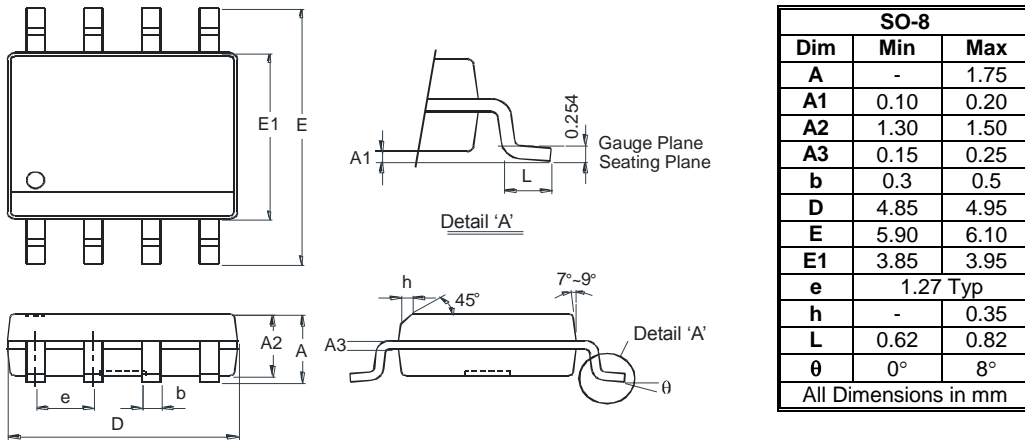


Fig. 12 Transient Thermal Response

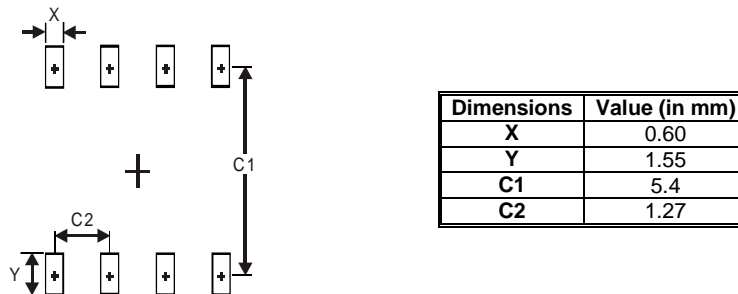
**Package Outline Dimensions**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



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